L Number	Hits	Search Text	DB	Time stamp
1	1	("6563216").PN.	USPAT	2004/09/06
2	688	257/499	USPAT;	06:40 2004/09/06
			US-PGPUB;	06:40
			EPO; JPO; DERWENT;	
	504		IBM_TDB	
3	531	257/500	USPAT; US-PGPUB;	2004/09/06
			EPO; JPO;	00.10
			DERWENT;	
5	370	257/501	IBM_TDB USPAT;	2004/09/06
			US-PGPUB;	06:40
			EPO; JPO; DERWENT;	
			IBM_TDB	
6	189	257/502	USPAT; US-PGPUB;	2004/09/06
			EPO; JPO;	06.40
			DERWENT;	
7	327	257/503	IBM_TDB USPAT;	2004/09/06
			US-PGPUB;	06:40
			EPO; JPO; DERWENT;	
:			IBM_TDB	
8	82	257/504	USPAT; US-PGPUB;	2004/09/06
			EPO; JPO;	00.40
			DERWENT;	
9	1774	257/499 257/500 257/501 257/502 257/503	IBM_TDB USPAT;	2004/09/06
		257/504	US-PGPUB;	06:41
			EPO; JPO; DERWENT;	
			IBM_TDB	
10	1131	(257/499 257/500 257/501 257/502 257/503 257/504) and (oxide or dioxide)	USPAT; US-PGPUB;	2004/09/06
		23773017 and (Oxide of dioxide)	EPO; JPO;	00.41
			DERWENT;	
11	690	((257/499 257/500 257/501 257/502 257/503	IBM_TDB USPAT;	2004/09/06
		257/504) and (oxide or dioxide)) and	US-PGPUB;	06:41
		(polysilicon or polycrystalline)	EPO; JPO; DERWENT;	
10	4.0-		IBM_TDB	0004/00/55
12	101	(((257/499 257/500 257/501 257/502 257/503 257/504) and (oxide or dioxide))	USPAT; US-PGPUB;	2004/09/06
		and (polysilicon or polycrystalline)) and	EPO; JPO;	
		cell and peripheral	DERWENT; IBM TDB	
13	299723	257/\$	USPAT;	2004/09/06
			US-PGPUB;	06:51
			EPO; JPO; DERWENT;	
17	120	///257/400 257/500 257/501 257/502	IBM_TDB	2004/00/05
17	130	(((257/499 257/500 257/501 257/502 257/503 257/504) and (oxide or dioxide))	USPAT; US-PGPUB;	2004/09/06
		and (polysilicon or polycrystalline)) and	EPO; JPO;	
		memory and peripher\$	DERWENT; IBM TDB	
18	16446	257/\$ and memory and peripher\$	USPĀT;	2004/09/06
			US-PGPUB; EPO; JPO;	06:52
			DERWENT;	
			IBM TDB	

19	1305	(257/\$ and memory and peripher\$) and (aspect adj ratio)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/06
			IBM TDB	
20	642	((257/\$ and memory and peripher\$) and (aspect adj ratio)) and trench	USPĀT; US-PGPUB; EPO; JPO;	2004/09/06 06:52
			DERWENT;	
21	606	(((257/\$ and memory and peripher\$) and (aspect adj ratio)) and trench) and (oxide or dioxide)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/06 06:53
22	589	(((257/499 257/500 257/501 257/502 257/503 257/504) and (oxide or dioxide)) and (polysilicon or polycrystalline)) not (((257/499 257/500 257/501 257/502	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/06 06:53
23	418	257/503 257/504) and (oxide or dioxide)) and (polysilicon or polycrystalline)) and cell and peripheral) ((((257/499 257/500 257/501 257/502 257/503 257/504) and (oxide or dioxide)) and (polysilicon or polycrystalline)) not (((257/499 257/500 257/501 257/502	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/06 07:06
		257/503 257/504) and (oxide or dioxide)) and (polysilicon or polycrystalline)) and cell and peripheral)) and (width or depth)	IBM_TDB	
24	3007	257/\$ and (trench near2 width)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/06 07:07
25	1583	(257/\$ and (trench near2 width)) and (trench near3 depth)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/06 07:07
26	1449	((257/\$ and (trench near2 width)) and (trench near3 depth)) and (oxide or oxide)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/06 07:07
27	1498	((257/\$ and (trench near2 width)) and (trench near3 depth)) and (oxide or dioxide)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/06 07:07
28	0	(((257/\$ and (trench near2 width)) and (trench near3 depth)) and (oxide or dioxide)) and memory and peripher	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/06 07:08
29	219	(((257/\$ and (trench near2 width)) and (trench near3 depth)) and (oxide or dioxide)) and memory and peripher\$	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/06 07:39
30	1279	(trench near3 depth)) and (oxide or dioxide)) not ((((257/\$ and (trench near2 width)) and (trench near3 depth)) and (oxide or dioxide)) and memory and	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 08:17
31	2	peripher\$) ("6642125").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/06 08:17